

ERRATUM

Paper entitled “Local and Global Simulations of Bridgman and Liquid-Encapsulated Czochralski Crystal Growth” by H. Zhang, L. L. Zheng, V. Prasad and D. J. Larson, Jr., pp. 865–873, November 1998.

Figure 7 of this paper is reproduced here in color to show the details of the temperature and flow fields.

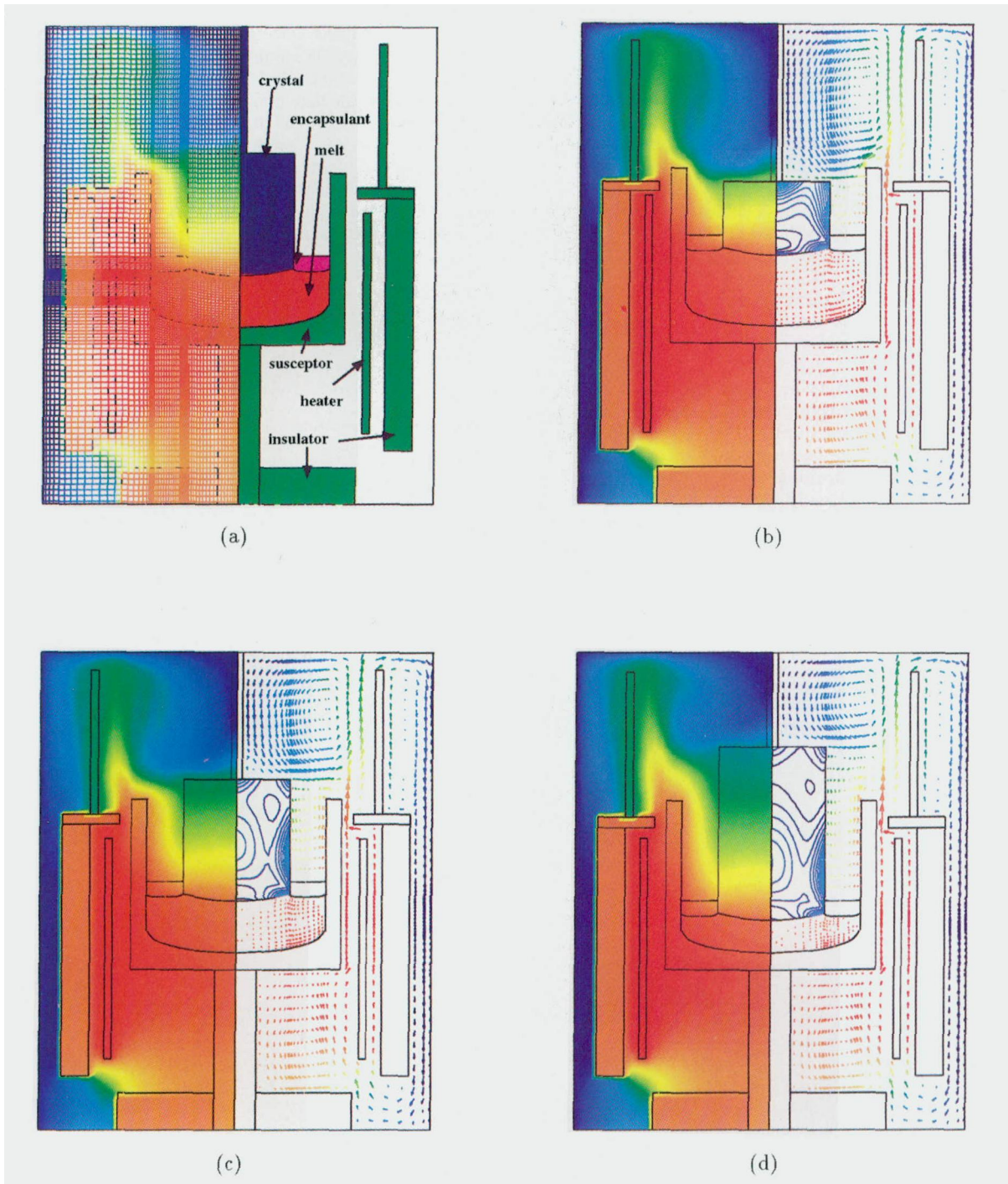


Fig. 7 Velocity, temperature, and von Mises stress fields in the crystal for a global simulation of GaAs growth with $Gr_g = 10^{10}$ and $Gr_l = 10^7$: (a) schematic and grid distribution, and represented for different crystal heights (b) 50 mm, (c) 80 mm, and (d) 110 mm